RoHS Compliant

MagnaChip

MDU1721VRH

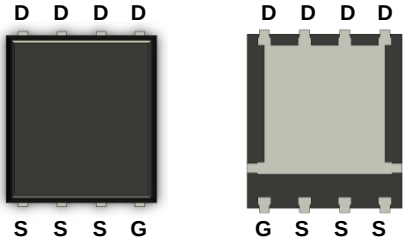
Single N-channel Trench MOSFET 40V, 100A, 1.4mΩ

General Description

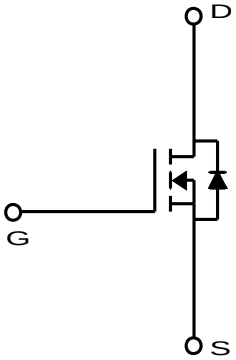
The MDU1721VRH uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDU1721VRH is suitable device for Synchronous Rectification For Server and general purpose applications.

Features

- V_{DS} = 40V
- I_D = 100A @V_{GS} = 10V
- $R_{DS(ON)}$ < 1.4mΩ @V_{GS} = 10V
- 100% UIL Tested
- 100% Rg Tested



PDFN56



Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current [1]	T_C=25°C (Silicon Limited)	I_D	204.1	A
	T_C=25°C (Package Limited)		100.0	
	T_C=100°C		129.1	
	T_A=25°C[3]		32.9[3]	
Pulsed Drain Current		I_{DM}	400.0	
Power Dissipation	T_C=25°C	P_D	96.2	W
	T_C=100°C		38.5	
	T_A=25°C[3]		2.5[3]	
Single Pulse Avalanche Energy [2]		E_{AS}	450	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	°C

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient [1]	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.3	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDU1721VRH	-55~150°C	PDFN56	Tape & Reel	Halogen Free

Electrical Characteristics (T_J =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D = 250μA, V_{GS} = 0V	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	-	3.0	
Drain Cut-Off Current	I_{DSS}	V_{DS} = 40V, V_{GS} = 0V	-	-	1.0	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±0.1	
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D =50A	-	1.1	1.4	mΩ
Forward Transconductance	g_{fs}	V_{DS} = 10V, I_D =50A	-	120	-	S
Dynamic Characteristics						
Total Gate Charge	$Q_{g(10.0V)}$	V_{DS} = 20.0V, I_D = 50.0A, V_{GS} = 10V	-	113.8	-	nC
Gate-Source Charge	Q_{gs}		-	23.3	-	
Gate-Drain Charge	Q_{gd}		-	18.6	-	
Input Capacitance	C_{iss}	V_{DS} = 20.0V, V_{GS} = 0V, f = 1.0MHz	-	7,450	-	pF
Reverse Transfer Capacitance	C_{rss}		-	200	-	
Output Capacitance	C_{oss}		-	1.850	-	
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = 10V, V_{DS} = 20.0V, I_D = 50A , R_G = 3.0Ω	-	24.0	-	ns
Rise Time	t_r		-	16.1	-	
Turn-Off Delay Time	$t_{d(off)}$		-	92.3	-	
Fall Time	t_f		-	30.0	-	
Gate Resistance	Rg	f=1 MHz	-	1.3	-	Ω
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	I_S = 50A, V_{GS} = 0V	-	0.80	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F =50A, dI/dt = 100A/μs	-	61.0	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	92.0	-	nC

Note :

1. Surface mounted FR-4 board by JEDEC (jesd51-7). Continuous current at T_C=25℃ is silicon limited
2. E_{AS} is tested at starting Tj = 25℃, L = 1.0mH, I_{AS} = 30.0A, V_{GS} = 10V.
3. T < 10sec.

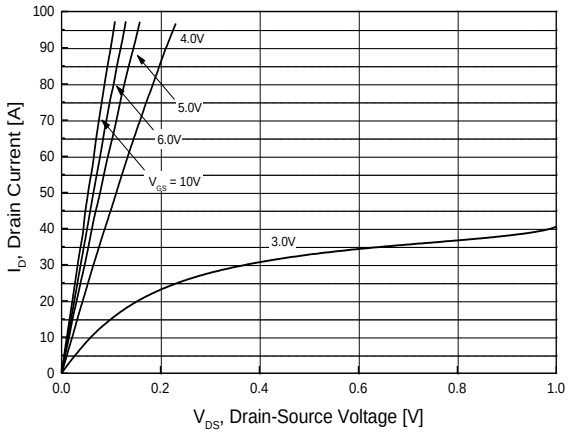


Fig.1 On-Region Characteristics

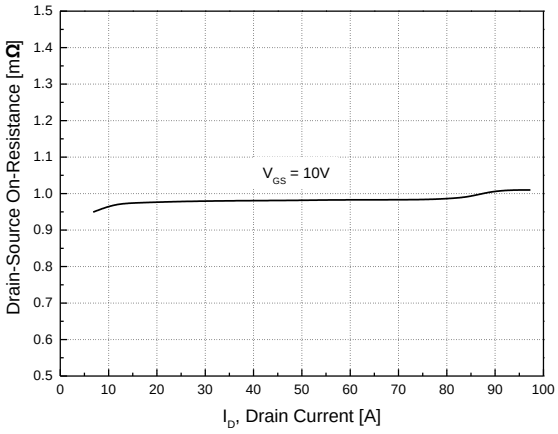


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

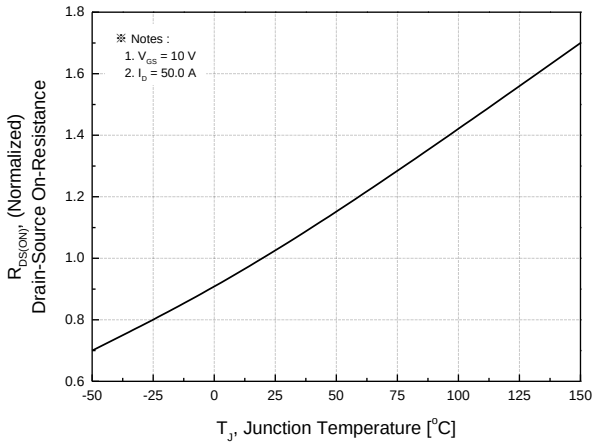


Fig.3 On-Resistance Variation with Temperature

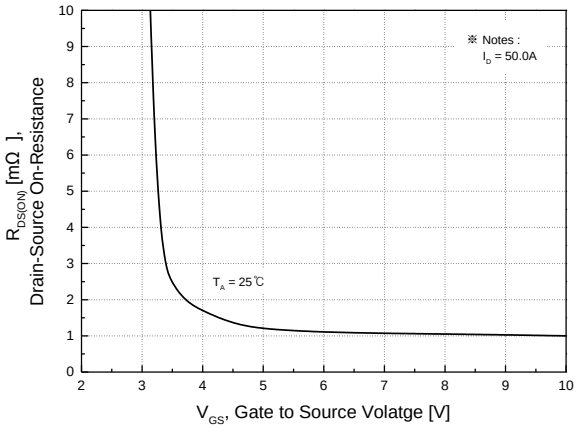


Fig.4 On-Resistance Variation with Gate to Source Voltage

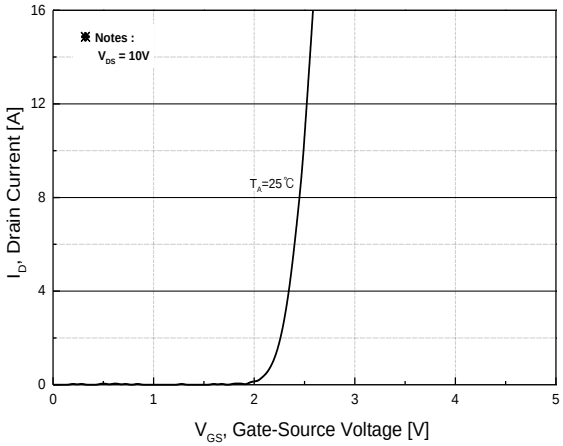


Fig.5 Transfer Characteristics

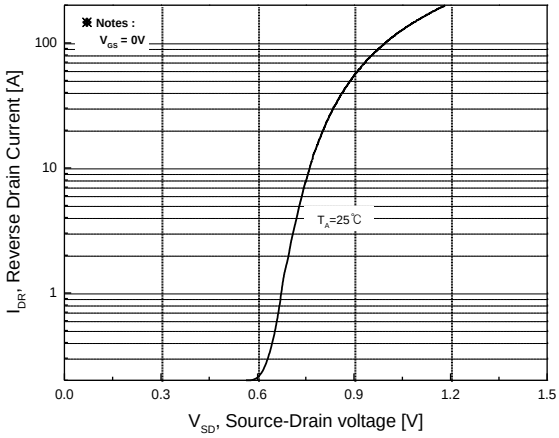


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

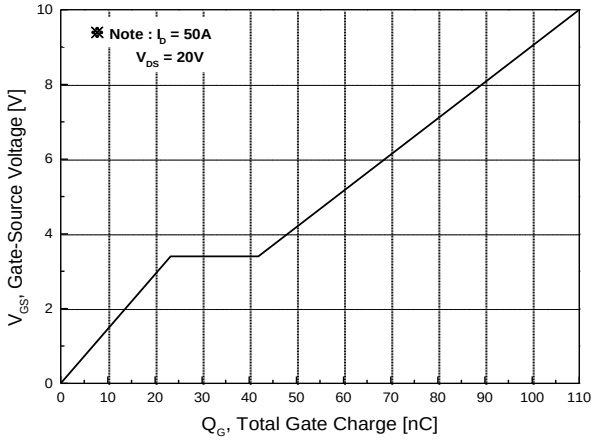


Fig.7 Gate Charge Characteristics

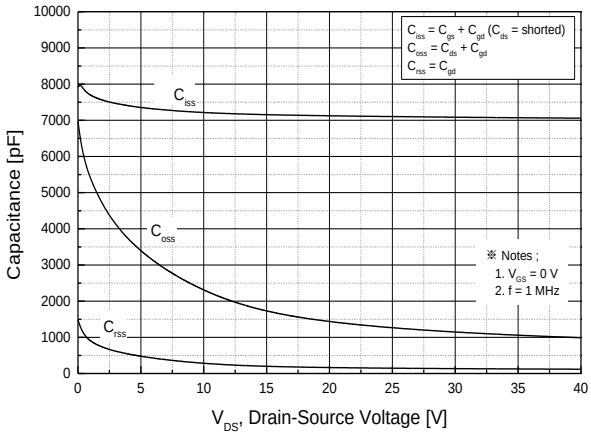


Fig.8 Capacitance Characteristics

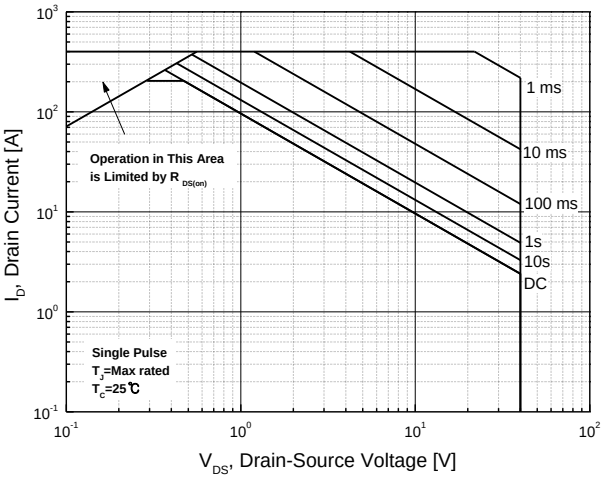


Fig.9 Maximum Safe Operating Area

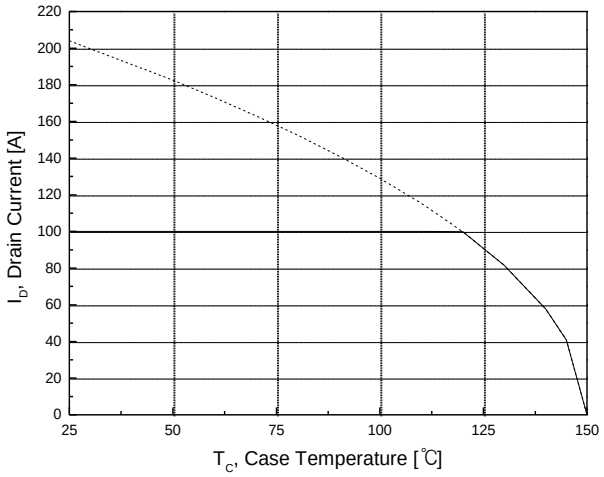


Fig.10 Maximum Drain Current vs. Case Temperature

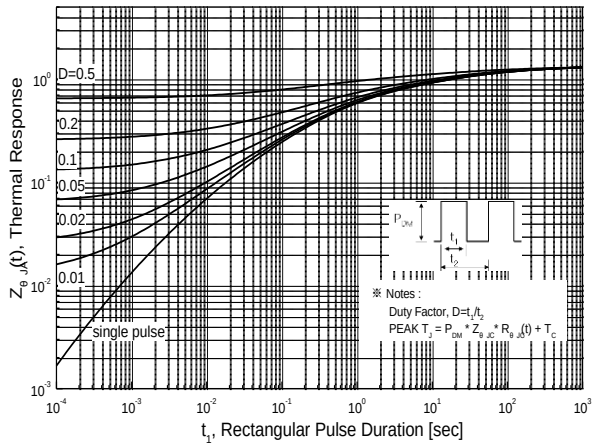
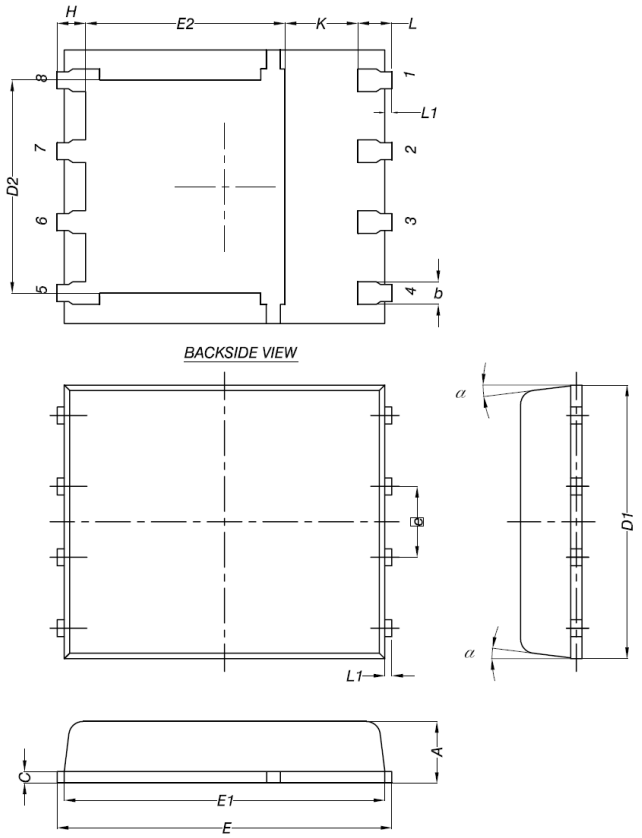


Fig.11 Transient Thermal Response Curve

Package Dimension

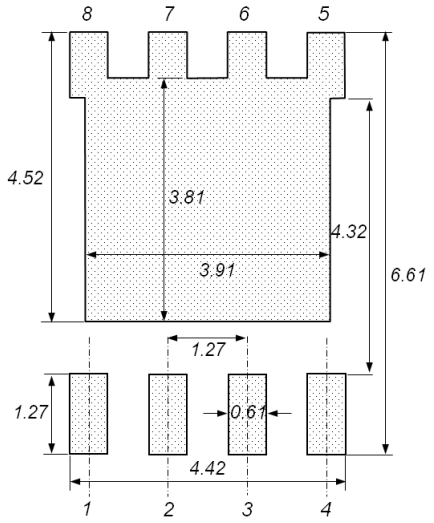
PDFN56 (5x6mm)

Dimensions are in millimeters, unless otherwise specified



Dimension	MILLIMETERS [mm]	
	Min	Max
A	0.90	1.10
b	0.33	0.51
C	0.20	0.34
D1	4.50	5.10
D2	-	4.22
E	5.90	6.30
E1	5.50	6.10
E2	-	4.30
e	1.27BSC	
H	0.41	0.71
K	0.20	-
L	0.51	0.71
L1	0.06	0.20
α	0°	12°

Land Pattern



DISCLAIMER:

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.